

Emerging Devices and Packaging Strategies for Electronic-Photonic AI Accelerators

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¹⁰ **Abstract:** The field of mimicking the structure of the brain on a chip is experiencing much interest
¹¹ driven by the demand for machine intelligent applications. However, the power consumption and
¹² available performance of machine-learning accelerating hardware still leaves much desire for
¹³ improvement. Application specific integrated circuits (ASIC) including emerging devices offer
¹⁴ intriguing algorithm-hardware homomorphism. In this letter, we share viewpoints, challenges,
¹⁵ and prospects of electronic-photonic neural network accelerators. Combining electronics
¹⁶ with photonics offers synergistic co-design strategies for high-performance AI ASICs and
¹⁷ systems. Harnessing signal processing advantages from photonics such as processing parallelism
¹⁸ deployed in tensor operation processors, high signaling speed, high fan-out enabling neuron
¹⁹ interconnectivity in neuromorphic architectures, and combining them with electronic logic
²⁰ control and data storage is an emerging prospect. However, the component library leaves much to
²¹ be desired for and is challenged by enormous size of photonic devices or challenge for retention-
²² of-state. Within this context, we will review the emerging electro-optic materials, functional
²³ devices, and systems packaging strategies that, when realized, provide significant performance
²⁴ gains and fueling the ongoing AI revolution. We discuss challenges that the field faces and
²⁵ offer a solution roadmap utilizing heterogeneous technology integration leading to a stand-alone
²⁶ photonics-inside AI ASIC 'black-box' for streamlined plug-and-play board integration in future
²⁷ AI processors.

²⁹ 1. Introduction

³⁰ Neuromorphic Photonics (NP) has gathered increasing interest in recent years owing to its
³¹ potential to disrupt performance of classes of applications that conventional digital processors are
³² challenged with attain [1]. Namely, artificial intelligence-based applications can be mapped to
³³ either tensor operation ASICs [2] or brain-inspired circuits such as neural networks, programmed
³⁴ via a learning procedure. Photonic circuits are well suited to high-performance signal processing
³⁵ implementations of neural networks for two predominant reasons: interconnectivity and high-
³⁶ bandwidth of linear and nonlinear operations. Neural networks require a large web of independent
³⁷ connections between layers containing individual neurons. Simply put, each connection between
³⁸ a pair of neuron needs a scalar weight value (or synaptic weight). If the output of a neuron
³⁹ layer can be represented by a vector, each neuron in a subsequent layer masks that vector by
⁴⁰ applying a dot product with a weight vector. This results in a layout of interconnections that can
⁴¹ be represented as a matrix-vector multiplication, or, for fully two-dimensional data such as for
⁴² image processing, as a matrix-matrix multiplication.

⁴³ It is possible to implement this multiplication via passive interferometric devices with tunable
⁴⁴ elements. For example, if an input vector is represented by wavelength-division multiplexed
⁴⁵ (WDM) optical signals, a weight can be applied by a sequence of tunable microring resonator

46 weights, called a weight bank [3]. In a scheme called broadcast and weight [4], these resonators
47 determine the interconnectivity as well as the weights. The nonlinearity can also be achieved
48 with an electrically tunable interferometer such as a microring resonators (MRR) or a Mach
49 Zehnder interferometers (MZI) [5].

50 Silicon photonics (SiPh) offers to integrate a high density of optoelectronic devices combined
51 with high quality passive components. It leverages the decades of research and development
52 from CMOS fabrication lines [6], and is gaining momentum as a dominant integrated photonic
53 platform driven by cost and chip performance alike [7]. The main limitations of a SiPh platform
54 for inference and machine-learning architectures lay on the lack of complex on-chip electronic
55 circuitry for calibration and control, as well as solutions for generating light on-chip efficiently.
56 In order to progress from early system demonstrations to fully integrated processors, NP systems
57 require new materials and technologies. For example, correcting fabrication variability in a post-
58 fabrication step can reduce heat dissipation and the amount of current needed for tuning. Memory
59 circuits that are able to interact directly with light can enable more agile reconfiguration in the
60 processor, as well as self-learning capabilities. Finally, information need to be transferred through
61 digital interfaces between electronic and photonic processors with minimal heat dissipation,
62 which can be achieved with integration of optical sources and high-efficiency modulators. In this
63 paper, we discuss potential solutions for these limitations, outlining key emerging devices that
64 can have an extraordinary impact on the performance of neuromorphic photonic processors.

65 **2. Moving Beyond Silicon Photonics**

66 In an electronic-photonic AI accelerator, the function and performance of a neural network a
67 tensor core processor rely strongly on the capability of realizing and implementing (i.e. WRITE,
68 READ, RESET, STORE operations) the weights and biases. These have to be applied to each
69 optoelectronic (or electronic) device representing either the weights during the machine learning
70 training step, or the trained weights during inference tasks. Depending on the specific application,
71 this requires precise phase and/or amplitude tuning (depending on the weighting scheme) of each
72 waveguide segments to realize the bit resolution of the selected machine learning task.

73 We can distinguish between weight requirements and hence implementation options for
74 classification versus machine learning [8] ('training', i.e. such as in cloud services e.g. Amazon
75 Web Service) applications of the underlying electronic-photonic ASIC accelerator (fig.1a);
76 while the update rate for classification is seldom (i.e. whenever a new data set is available
77 producing updated weights) during training step, the weights and biases need to be updated
78 constantly. This naturally leads to non-volatile state-retention for classification as compared to
79 rapid (faster-the-better) WRITE-RESET-REWRITE etc cycles for cloud training applications.
80 Specifically at the network edge the size-weight-area-performance (SWAP) requirements of
81 AI systems are demanding, including high energy efficiency, hence stressing the non-volatile
82 capability of the deployed weight-memory; that is, once the weights are WRITTEN, they (ideally)
83 are zero-power consuming static functions. For memory options, electronics offers a variety of
84 memory options with the trade-off between WRITE-speed and energy vs. READ latency and
85 include cache, SRAM, DRAM, FLASH (in increasing retention-time order). Interestingly, a
86 brief analysis suggests a 100x superior potential of photonic memory over state-of-art SRAM
87 with respect to data baud rate (speed) and memory access energy; in brief, an SRAM has an
88 access latency of 0.3ns costing about 100fJ/access. A photonic memory based on phase-change-
89 materials (PCM), once WRITTEN, requires only the photon creation and detection energies.
90 The minimum power of foundry-based PIC detectors in the C-band, for example, are about
91 50nW for signals above 30GHz. Assuming a 1% efficiency for the laser wall-plug efficiency and
92 optical losses on the PIC and coupling to the PIC [1-2dB per coupler], a memory READ (access)
93 energy of a PCM-written photonic random-access memory (P-RAM) takes <1fJ/access for an
94 on-off-keyed (OOK) signal at 30GHz data rates, or, about 10fJ/access for a higher bit resolution

95 (e.g. PAM16 for a 4-bit ML classifier). Thus, a generic photonic link offers MAC operations
96 and memory access of 10-100x higher MAC/s/J/access than SRAM. Following this potential
97 for PIC-based MAC acceleration, electro-optic reconfigurable photonic integrated circuits (PIC)
98 have been predicted [9] and demonstrated [5] to process the repeating convolution-underlying
99 MAC operation (multiply-accumulate) in inference tasks on off-chip trained kernels.

100 Exploring the memory-(active)material relationship further; PCMs have recently shown
101 promising capability, both as amplitude and phase modulation [10], exploiting the non-volatile
102 switching between their amorphous and crystalline states. In conventional SiPh, this is achieved by
103 either heating elements placed near a waveguide, or by doping the waveguide with a p-n junction.
104 These approaches rely on the thermo-optic effect and the free-carrier depletion (FCD) effect,
105 respectively. But, since they require constant active electrical current, their energy-efficiency is
106 limited. PCMs are non-volatile and requiring no active energy consumption, making them ideal
107 for fabrication variation trimming as well as optical memory for edge AI applications. The FCD
108 effect in silicon being weak requires high voltages to achieve significant index modulation. This
109 inefficiency is problematic because neurons and tensor weight updates require a sufficient
110 modulation so that small signals can span all features of the nonlinear activation function [11].
111 Better results, that is micrometer compact MZI modulators at GHz speeds could be obtained
112 using free-carrier-based electro-optic modulation such as in the material Indium Tin Oxide
113 (ITO) [12], as enabled by unity-strong index modulation [13].

114 2.1. Emerging Materials for Non-volatile Optical Memory

115 **Why is memory important?** Memory is key element of all the modern computer, as CPU keeps
116 transferring data and instructions from and to the memory side of the computer. On the optical
117 side, non-volatile optical materials have the potential to play the same role, allowing to store
118 phase and amplitude variation on a photonic circuit. As NP links a large web of interconnect
119 synapses, having a precise and non-volatile control of the synaptic weights is essential. The PCM
120 recently became one of the most popular and promising active materials for the realization of this
121 type of non-volatile multilevel random access photonic memory (P-RAM).

122 In recent days, the widely studied PCMs include transition metal oxide, chalcogen-based and
123 antimony based PCMs, such as vanadium VO₂, Ge₂Se₂Te₂ (GST), Ge₂Sb₂Se₄Te₁ (GSST),
124 Ge₂Sb₂Se₂ (GSSE), and Sb₂Se₃. All those materials are embedded into silicon-based photonic
125 devices whose phase can be reversibly changed between crystalline and amorphous via appropriate
126 heating processes. The photonic properties of the material between the two phases are
127 significantly different with distinct refractive index (n/k) contrast which divides nonvolatile pro-
128 grammable PIC memories into two groups: phase-shifting modulation, and amplitude modulation.

129
130 For the phase-only modulation, a variety of PCMs is embedded into resonate-based PICs
131 such as MZI, micro-ring resonators, and directional couplers [14, 15, 17]. Vanishingly small
132 insertion loss, large index contrast (Δn) PCMs such as GSST4 and Sb₂Se₅ are preferred in the
133 telecommunication bands that confers low insertion loss, small footprint, and non-static power
134 consumption.

135 For amplitude-only modulation, the variety of large index contrast (Δk) and small insertion loss
136 in amorphous state PCMs are covered over the silicon-based waveguide such as GSSE and GST
137 [10, 16].

138 To trigger the structural transition of PCM, the local annealing is required to apply on the material
139 which normally relies on the external laser heating, or the micro-resistive heater to actuate
140 structural phase transition via multi-electrical pulse combinations. From the perspective of
141 overall footprint and phase transition energy efficiency, external laser heating is a better option
142 compared to micro-heating since the pump laser can be directly guided to the target material as a
143 heating source without extra structure on-chip needed. On the other hand, for micro-resistive

Non-Volatile Edge	Volatile (10GHz) Cloud
High	Medium

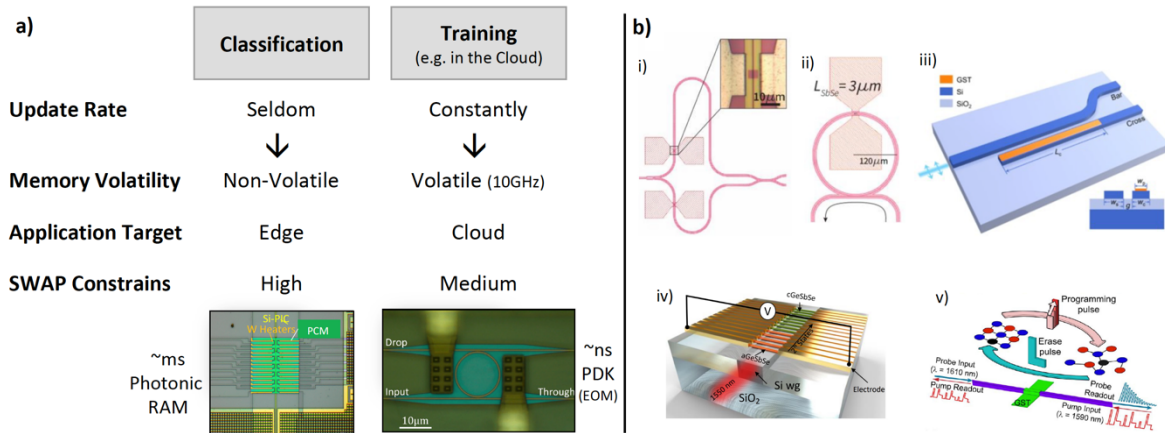


Figure. 1. Performance of the AI ASIC weights and biases rely on the material of the reconfigurable memory devices. (a) Memory requirements depend on the machine learning application such as classification vs. machine-learning training [8]. (b) Photonic random-access-memory (P-RAM) options from the recent literature include multi-state memories [10]. i) An unbalanced MZI with Sb_2Se_3 cell [14]. ii) Micro-ring resonator with a Sb_2Se_3 [14]. iii) A 1x2 directional coupler with GST cell [15]. iv) Waveguide with GSe cell and multiple double-sided tungsten heaters [10]. v) Schematic of the laser pulse to amorphized and crystallize the integrated phase-change photonic memory cell [16]. Interestingly, one finds a 10-100 fold higher speed-energy product performance (for the memory READ step) of P-RAMs when compared to SRAM technology.

144 heaters such as Tungsten, Graphene, or ITO heaters, though they need extra space for contact
 145 pads and routing, the programming setup is relatively simpler compared to the external heating.
 146 This is especially true for the large-scale NPs which require a large amount of PCM memories
 147 for the weight banks, as they could be easily controlled through electrical control unit instead
 148 of multiple modulated external laser sources. A mix of the two approaches might combine the
 149 best parts of both, having larger post-fab trimming with laser heating, and fast tuning with local
 150 electrical heaters. All these developments of PCM-based PRAMs are the fundamental steps
 151 towards the fast, lower-power consumption, high bit resolution on-chip photonics memory for
 152 neuromorphic computing.

153 2.2. Efficient Modulator Materials for Silicon Photonics

154 Current p-n junction-based SiPh platforms do not support highly-interconnected photonic neural
 155 networks unless they use (a) more sensitive modulators, (b) active transimpedance amplifiers
 156 (TIAs), or (c) operate at a sub-GHz bandwidth [11]. This occurs because modulators need a
 157 large voltage swing to reach the nonlinear threshold in their nonlinear transfer function, which
 158 suppresses noise directly between one neural layer and the next – a requirement for cascadable
 159 analog links. This swing can either be achieved by increasing optical pump power at the
 160 modulator or by providing electric transimpedance gain. However, optical gain is limited by
 161 optical nonlinearities in waveguides (and potentially power budgets), whereas transimpedance
 162 gain is inversely proportional to the bandwidth of the circuit.

163 In order to construct O/E/O neurons compatible with SiPh that can operate at >10 GHz, we
 164 need a modulator that has simultaneously a low-capacitance (RC limited) and a low- V_{pi} (e.g.
 165 50 mV). Comparing the $V_n L$ parameter, while p-n junctions are limited to $360 V\mu m$, other
 166 heterogeneously devices could reach the wanted performances, such as ITO-based modulator
 167 that can reach $95 V\mu m$ [13], and ITO-graphene device, that can implement even high-bandwidth
 168 modulation, up to more than 130 GHz [18]. Exploiting the properties of these materials allows
 169 to create more specific devices such as the Non-Linear Activation Functions for NP.

170 3. System Integration Strategies for Electronic-Photonic AI ASICs

171 While PCMs help enable an efficient electrical reconfiguration medium, they require precise
172 analog inputs and an electronic control framework. Unless the required analog signals can be
173 generated and detected on-chip from a smaller set of inputs (through e.g. monolithic integration),
174 each component requires its own electrical bondpads for interfacing with an external control chip.
175 For large-scale neuromorphic circuits, this means the chip's footprint is dominated by electrical
176 routing and thermal constraints. Because photonic devices are limited in size by the lightwave's
177 wavelength, PICs are fabricated using lithographic methods from previous node generations as
178 current CMOS. As a result, PICs are expected to have a larger area than CMOS ASICs, and can
179 also serve as an interposer between the CMOS ASIC and the PCB.

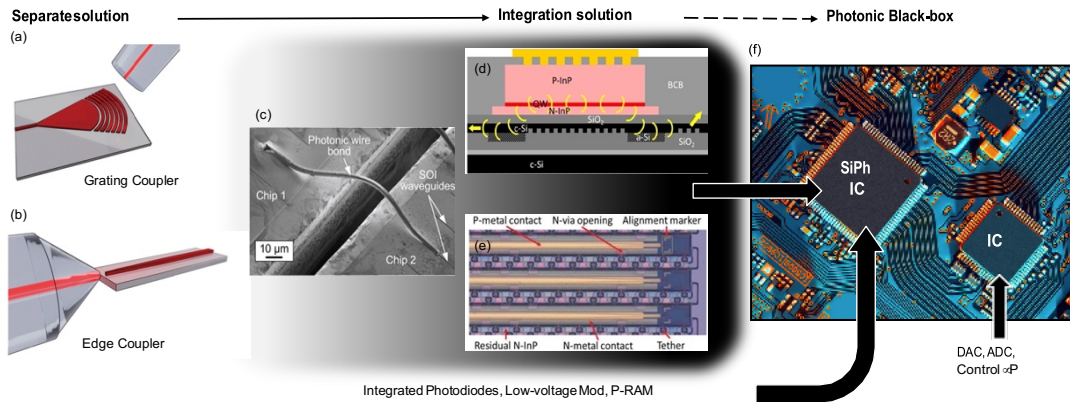


Figure. 2. Example of I/O integration for PIC. a-b) Well-known coupling structures, such as Grating Couplers and Edge couplers [19]. c) Example of Photonic Wire Bonding connecting laser to PIC [20]. d) Back-side-on-BOX heterogeneously integrated III-V- on-silicon [21]. e) Hybrid integrated semiconductor using Micro-Transfer-Printing [22]. f) Graphical representation of the Photonic Black-box, where all the optical components are inside a single IC having just electrical I/O.

180 While electrical connectivity can borrow industry standards from the semiconductor manufac-
181 turing industry, optical interfaces are less matured, yet recent development give promise for an
182 efficient and salable optical I/O driving ultimate PIC-electronic integration, as shown in fig. 2.
183 Today, signal I/O is generally addressed by utilizing coupling structures such as grating couplers,
184 or edge couplers. These solutions show low insertion loss (as low as 0.5dB [19]) but still rely on
185 sub-micron alignment of fibers. More recently, promising research on optical source integration
186 surfaced. One solution is termed photonic wirebonding [20], which can connect arbitrarily placed
187 devices on the same interposer or substrate. This approach has the most potential in the short
188 term, enabling integration of existing solutions into one single platform.

189 Full integration of lasers on silicon has been demonstrated by a different research groups.
190 Notable examples include Back-side-on-BOX heterogeneously integrated III-V-on-silicon [21],
191 quantum dots on silicon [23], and hybrid integrated semiconductor [22]. Integrated optical sources
192 on silicon represents a substantive push for AI ASIC hardware and subsequent applications,
193 because it can be miniaturized and deployed in the field, where edge AI processing is the most
194 bottlenecked, while supporting more stringent vibration and temperature fluctuation requirements.
195 Moreover, chips can be assembled at-scale (volume) without requiring advanced optical packaging,
196 which will likely offset the increased fabrication cost due to heterogeneous integration [24]. Our
197 vision and ongoing explorations are to co-integrate photonics-inside, fully-packaged 'black-box'
198 photonic ASIC accelerators on the same printed circuit boards (PCB) as electronic ICs (fig.
199 2(f)). This will revolutionize not only photonic AI hardware prototyping, but also ripple
200 through the entire PIC community; offering an stand-alone photonic system (including source,
201 programmable circuit, and O-E back-end) results in an 'photonic-hidden' module that electronic

202 circuit designers can use as a plug-and-play design module without having to have much (possibly
203 'any') understanding of the optical details.

204 **4. Concluding Remarks**

205 Here we review latest advances in photonic programmable circuits and devices for realizations of
206 electronic-photonic ASICs for machine-learning (ML) applications. Here, we discuss relevant
207 material- and device design options, which are the underlying fabric of these emerging mixed-
208 signal AI and ML processors processor. We analyze the requirements for the machine-learning
209 weights and biases by distinguishing between classification (inference) vs. training applications.
210 For each, we find a different set of device and hence 'active' (programmable) performance
211 requirements. For network edge applications with rare weight-updating, implementing non-
212 volatile photonic random-access-memory (P-RAM) suggests a 10-100 times higher baudrate-energy
213 performance for WRITTEN weights, i.e. the memory READ step. Furthermore, we show
214 examples of how the nonlinear activation function can be efficiently realized for neuromorphic
215 ASICs, for which micrometer compact ITO-based modulators show great promise being 10,000
216 more compact than modulators based on thin-film Lithium Niobate. Finally, we share our vision
217 and ongoing effort of developing the first photonics-inside (and hidden from the electronic
218 circuit designer) fully packaged photonic AI processor. This co-design strategy leverages recent
219 developments in photonic-wirebonding to same-chip integrate lasers onto silicon PICs. With
220 this, we believe, the future for photonic-electronic ASICs is rather 'bright' as we are just starting
221 to explore fully co-packaged AI systems. However, CMOS foundries still do not allow materials
222 such as most PCMs and ITO, due to low demand and process compatibility issues. Future work
223 should face these challenges while considering new materials. Moreover, integration of lasers
224 source still requires additional steps in the fabrication process, still facing mass production
225 limitation. As it stands, solutions for neural network weights or kernels for tensor operation
226 accelerators (including convolution acceleration) are being realizable in the prototyping stages
227 at-present. Indeed, some of these challenges can be overcome by the increasing demand in AI
228 hardware and circuits, which should drive implementations of exploratory pilot lines in the
229 foundries that offer material-device-packaging opportunities beyond silicon-only circuits.

230

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